

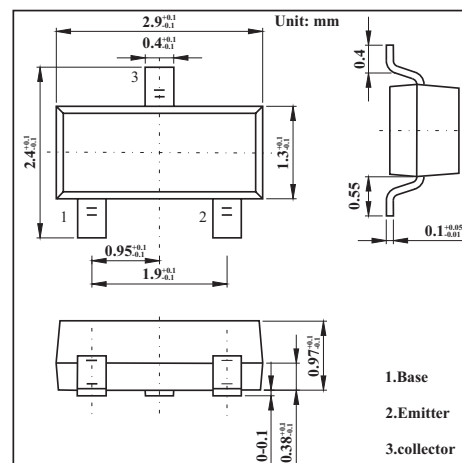
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- Low collector saturation voltage: $V_{CE}=0.25V(\text{Max.})$
- Low output capacitance: $C_{ob}=2pF(\text{Typ.})$
- Transistor NPN

MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-base voltage	VCBO	60	V
Collector-emitter voltage	VCEO	50	V
Emitter-base voltage	VEBO	5	V
Collector current	IC	150	mA
Collector dissipation	PC	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	- 5 5 t o + 1 5 0	°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BVCBO	IC=100iA , IE=0	60			V
Collector-emitter breakdown voltage	BVCEO	IC=1mA , IB=0	50			V
Emitter-base breakdown voltage	BVEBO	IE=10iA, IC=0	5			V
Collector cutoff current	ICBO	VCB=60V, IE=0			0.1	iA
Emitter cutoff current	IEBO	VEB=5V, IC=0			0.1	iA
DC current transfer ratio	hFE	VCE=6V, IC=2mA	70		700	
Collector-emitter saturation voltage	VCE(sat)	IC/IB=100mA/10mA			0.25	V
Transition frequency	fT	VCE=10V, IC=1mA,	80			MHz
Output capacitance	Cob	VCB=10V, IE=0, f=1MHz		2	3.5	pF
Noise figure	NF	VCE=6V, IC=0.1mA, f=1KHz, Rg=10kÙ			10	dB